Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	266798	(dice dicing separation separat$3 cutting cut$2 dividing divid$3 singularity individual single) near5 (wafer substrate workpiece)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/11/10 12:53
L2	52647	1 and (dice dicing separation separat$3 cutting cut$2 dividing divid$3 singularity individual single) near5 (mark line groove void dicing near3 line)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/11/10 15:31
L4	7133	2 and (dice dicing separation separat$3 cutting cut$2 dividing divid$3 singularity individual single mark line groove void dicing near3 line) near5 laser	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/11/10 12:57
L5	9928	2 and (dice dicing separation separat$3 cutting cut$2 dividing divid$3 singularity individual single mark line groove void dicing near3 line) near5 (laser beam)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/11/10 12:49
L6	9300	2 and (dice dicing separation separat$3 cutting cut$2 dividing divid$3 singularity individual single mark line groove void dicing near3 line) near4 (laser beam)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/11/10 12:49
L7	8342	2 and (dice dicing separation separat$3 cutting cut$2 dividing divid$3 singularity individual single mark line groove void dicing near3 line) near3 (laser beam)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/11/10 12:49
L8	97293	(dice dicing separation separat$3 cutting cut$2 dividing divid$3 singularity individual single) near5 (laser irradiat$3)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/11/10 12:50

L9	38078	(dice dicing separation separat$3 cutting cut$2 dividing divid$3 singularity individual single) near (laser irradiat$3)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/11/10 12:51
L10	150634	(dice dicing separation separat$3 cutting cut$2 dividing divid$3 singularity individual single) with (laser irradiat$3)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/11/10 12:53
L11	34413	(dice dicing separation separat$3 cutting cut$2 dividing divid$3 singularity individual single) with (polish$3)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/11/10 12:59
L12	3193	(dice dicing separation separat$3 cutting cut$2 dividing divid$3 singularity individual single) with (blasting)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/11/10 12:52
L13	37455	11 or 12	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/11/10 12:52
L14	4772	10 and 13	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/11/10 12:53
L15	2541	14 and (dice dicing separation separat$3 cutting cut$2 dividing divid$3 singularity individual single) near5 (wafer substrate workpiece)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/11/10 12:55
L16	1165	15 and (dice dicing separation separat$3 cutting cut$2 dividing divid$3 singularity individual single) near5 (die chip "IC")	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/11/10 12:56
L17	4170	(mark line groove void dicing near3 line) near5 (laser near5 irradiat$3)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/11/10 12:58

L18	87	17 and (dice dicing separation separat$3 cutting cut$2 dividing divid$3 singularity individual single) .with (polish$3)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/10 15:29
L19	1	10/601310	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/10 14:08
L20	151	17 and (dice dicing separation separat$3 cutting cut$2 dividing divid$3 singularity individual single) with (polish$3 grind$3)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/10 15:46
L21	168	1 and (dice dicing separation separat$3 cutting cut$2 dividing divid$3 singularity individual single) near5 (mark line groove void dicing line perforat$3) near5 (laser near3 irradiat$3)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/10 15:43
L22	37	21 and (dice dicing separation separat$3 cutting cut$2 dividing divid$3 singularity individual single) with (polish$3 grind$3)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/10 15:53
L23	1	(separation adj groove near5 laser adj beam and polishing and individually adj dividing).clm.	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/10 15:55
S5	129251	semiconductor and ((dice dicing separation separat$3 cutting cut$2 dividing divid$3 singularity individual single) near5 (wafer substrate workpiece))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/11/10 12:39
S14	24785	S5 and ((dice dicing separation separat$3 cutting cut$2 dividing divid$3 singularity single) near5 (line groove alignment adj mark))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/07 08:38

S15	1142	S14 and ((dice dicing separation separat$3 cutting cut$2 dividing divid$3 singularity singleline groove alignment adj mark) near5 (polish$3 blast$5))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/07 08:42
S16	1530	S14 and ((dice dicing separation separat$3 cutting cut$2 dividing divid$3 singularity single line groove alignment adj mark) near5 (polish$3 blast$5))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/07 08:41
S17	67	S16 and ((dice dicing separation separat$3 cutting cut$2 dividing divid$3 singularity singleline groove alignment adj mark) near5 (laser near5 beam))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/07 13:49
S18	22	(gate near5 silicide) with (silicide near5 protect$3 near3 mask)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/07 14:05
S19	1	10/456985	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/07 13:55
S20	1	10/758289	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/07 13:56
S21	2	(gate near5 silicide) with (silicide near5 protect$3 near3 mask) with simultaneously	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/07 14:25
S22	275	(gate near5 silicide) with simultaneously	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/07 14:04
S23	2	S22 and simultaneously with (silicide near5 protect$3 near3 mask)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/07 14:05

S24	5	S22 and (silicide near5 protect$3 near3 mask)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/07 14:11
S25	22	S22 and (silicid$6 near5 protect$3 near3 (mask$3 layer))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/07 14:18
S26	5	S22 and (silicid$6 near5 protect$3 near3 (mask$3 layer)) with simultaneously	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/07 14:22
S27	5	(gate near5 silicide) with (silicide near5 protect$3 near3 (mask$3 layer)) with simultaneously	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/07 14:35
S28	0	(image near3 semsor) with (implantation implating implant$3)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/07 14:36
S29	0	(image near3 sesor) with (implantation implating implant$3)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/07 14:36
S30	260	(image near3 sensor) with (implantation implating implant$3)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/07 14:36
S31	143	S30 and (resist photoresist mask$4) with (implantation implating implant$3)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/07 14:42
S32	40	S31 and (resist photoresist mask$4) with (thick thickness)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/07 14:43
S33	40	S32 and (resist photoresist mask$4 thick thickness)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/07 14:43
S34	32	S33 and (resist photoresist mask$4 thick thickness) near5 first	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/07 14:44

S35	28	S34 and (resist photoresist mask$4 thick thickness) near5 second	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/08 08:15
S36	1	10/745988	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/07 14:47
S37	0	10/816729	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/08 09:07
S38	1	10/816958	US-PGPUB; USPAT; EPO; JPO	OR	ON	2005/07/08 09:07